

Topological insulators based on layers and foils for thermoelectric microcooling devices

Albina NIKOLAEVA, Leonid KONOPKO, Tito HUBER, Igor GHERGHISHAN, George PARA, Denis NIKA

<https://doi.org/10.1109/CAS59036.2023.10303669>

Abstract

We present the results of the study on thermoelectric properties and oscillatory effects (layers and foils) based on p-type Bi_2Te_3 topological insulators and n-type $\text{Bi}_{0.84}\text{Sb}_{0.16}$ foils ($d=10-20 \mu\text{m}$). Analysis of the Shubnikov de Haas oscillations of p-type Bi_2Te_3 single-crystal layers has confirmed the presence of surface states in layers with a high quantum charge carrier mobility of up to $20 \times 10^3 \text{ cm}^2/(\text{V s})$ and a Fermi surface anisotropy of $A = 4$, which are characteristic of bulk topological insulator. It has been revealed that the thermal conductivity of the foils in a temperature range of 300-100 K remains constant. Based on a technology developed by the authors for forming unsupported p-type Bi_2Te_3 single-crystal micro-layers and an n-type $\text{Bi}_{0.84}\text{Sb}_{0.16}$ foils a device was constructed that provides a temperature gradient of $\Delta T = 9 \text{ K}$ over an area of 0.01 cm^2 . Structures based on Bi_2Te_3 can be used to design miniature sensors for thermoelectric devices, such as thermoelectric coolers, in particular, for cooling a computer processor.

Keywords: bismuth telluride, microcooler, foil, microlayers, thermoelectricity, topological insulators

References:

1. D.V. Rowe, *Thermoelectric handbook: macro to nano*, Boca Raton: Taylor Francis, pp. 1008, 2006. [Google Scholar](#)
2. O. Yamashita, S. Tomiyoshi and K. Makita, "Bismuth telluride compounds with high thermoelectric figures of merit", *Journal of Applied Physics*, vol. 93, pp. 368-374, 2003. [CrossRef](#) [Google Scholar](#)
3. Takahashi Ryuji and Murakami Shuichi, "Thermoelectric transport in topological insulators in the spin helical Dirac transport regime", *Nature*, vol. 460, pp. 1101-1105, 2009. [Google Scholar](#)

2023 International Semiconductor Conference (CAS)

11-13 October 2023, Sinaia, Romania, eISBN 979-83-50323-95-5

4. J.P. Heremans, "Low dimensional thermoelectricity", *Acta Physica Polonica*, vol. 108, pp. 609-634, 2005. [CrossRef Google Scholar](#)
5. O. Rabin, Y.M. Lin and M.S. Dresselhaus, "Anomalously high thermoelectric figure of merit in Bi_{1-x}Sb_x nanowires by carrier pocket alignment", *Appl Phys Lett*, vol. 79, pp. 81-83, 2001. [CrossRef Google Scholar](#)
6. P. Lardson, S.D. Mahanti and M.G. Kanatzidis, "Electronic structure and transport of Bi₂Te₃ and BaBiTe₃", *Phys.Rev. B*, vol. 61, pp. 8162-8171, 2000. [CrossRef Google Scholar](#)
7. V. Goyal, D. Teweldebrhan and A. Balandin, "Mechanically-exfoliated stacks of the films of Bi₂Te₃ topological insulator", *Appl Phys Lett*, vol. 97, pp. 133117, 2010. [CrossRef Google Scholar](#)
8. A.V. Demidchik and V.G. Shepelevich, "Structure and electronic spectrum of fullerene-like nanoclusters based on Mo Nb Zr and Sn disulfides", *Inorganic Materials*, vol. 40, pp. 391-395, 2004. [CrossRef Google Scholar](#)
9. L. Konopko, A. Nikolaeva, T. Huber and D. Meglei, "Thermoelectric properties of Bi₂Te₃ microwires", *Phys. Status Solidi C*, vol. 11, pp. 1377-1381, 2014. [CrossRef Google Scholar](#)